Title (en)

MAGNESIUM OXIDE SPUTTERING APPARATUS

Title (de)

VORRICHTUNG ZUM SPUTTERN DES MAGNESIUMOXYDS

Title (fr)

APPAREIL DE PULVERISATION CATHODIQUE D'OXYDE DE MAGNESIUM

Publication

EP 0970261 A1 20000112 (EN)

Application

EP 98912942 A 19980317

Priority

- US 9805143 W 19980317
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Abstract (en)

[origin: WO9842890A1] This invention relates to a method and apparatus for high rate reactive sputtering. Particularly, the invention relates to a method and apparatus of sputter depositing reacted metal-compound films where the sputter deposition rate approaches the deposition rate of the unreacted metal. More particularly, the invention relates to an apparatus wherein the sputter deposition target is placed at a greater than usual distance from the substrate and the target metallic erosion track is confined to a narrower width than is typical in current systems.

IPC 1-7

C23C 14/35; H01J 37/34

IPC 8 full level

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CPC (source: EP KR)

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Citation (search report)

See references of WO 9842890A1

Cited by

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CH DE FR LI

DOCDB simple family (publication)

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